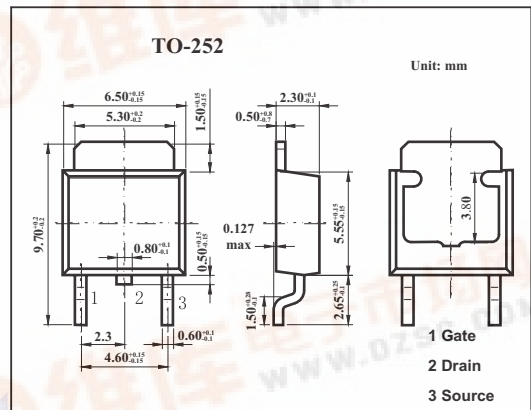
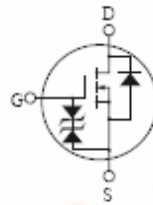


SMD Type MOSFET

N-Channel Silicon MOSFET  
2SK2926S

Features

- Low on-resistance  
R<sub>DS</sub> = 0.042 Ω typ.
- High speed switching



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V <sub>DSS</sub>	60	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	15	A
	I <sub>DP</sub> *	60	A
Power dissipation	P <sub>D</sub>	25	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 μs, Duty Cycle ≤ 1%

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain to source breakdown voltage	V <sub>DSS</sub>	I <sub>D</sub> = 10mA, V <sub>GS</sub> = 0	60			V
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0			10	μA
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0			±10	μA
Gate to source cutoff voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	1.5	2.5		V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 8A	7	11		S
Drain to source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 8A		0.042	0.055	Ω
		V <sub>GS</sub> = 4V, I <sub>D</sub> = 8A		0.065	0.11	Ω
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1MHz		500		pF
Output capacitance	C <sub>oss</sub>			260		pF
Reverse transfer capacitance	C <sub>rss</sub>			110		pF
Turn-on delay time	t <sub>on</sub>	I <sub>D</sub> = 8A, V <sub>GS(on)</sub> = 10V, R <sub>L</sub> = 3.75 Ω		10		ns
Rise time	t <sub>r</sub>			80		ns
Turn-off delay time	t <sub>off</sub>			100		ns
Fall time	t <sub>f</sub>			110		ns

